

Dongri Qiu

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/3474713/publications.pdf>

Version: 2024-02-01

18
papers

297
citations

840776

11
h-index

996975

15
g-index

18
all docs

18
docs citations

18
times ranked

637
citing authors

#	ARTICLE	IF	CITATIONS
1	Hole Conduction of Tungsten Diselenide Crystalline Transistors by Niobium Dopant. <i>Advanced Electronic Materials</i> , 2019, 5, 1800695.	5.1	7
2	Formation of transition metal dichalcogenides thin films with liquid phase exfoliation technique and photovoltaic applications. <i>Solar Energy Materials and Solar Cells</i> , 2018, 184, 9-14.	6.2	16
3	Recent Advances in Synthesis and Assembly of van der Waals Materials. <i>Journal of the Korean Physical Society</i> , 2018, 73, 805-816.	0.7	11
4	Locally Gated SnS ₂ /hBN Thin Film Transistors with a Broadband Photoresponse. <i>Scientific Reports</i> , 2018, 8, 10585.	3.3	21
5	Selective control of electron and hole tunneling in 2D assembly. <i>Science Advances</i> , 2017, 3, e1602726.	10.3	25
6	Electrical and photovoltaic properties of residue-free MoS ₂ thin films by liquid exfoliation method. <i>Nanotechnology</i> , 2017, 28, 195703.	2.6	18
7	High photoresponsivity from multilayer MoS ₂ /Si heterojunction diodes formed by vertically stacking. <i>Journal of Applied Physics</i> , 2017, 122, .	2.5	11
8	Enhancement of near-infrared detectability from InGaZnO thin film transistor with MoS ₂ light absorbing layer. <i>Nanotechnology</i> , 2017, 28, 475206.	2.6	26
9	Semiconducting properties of perchlorate-doped graphene using an electrochemical method. <i>RSC Advances</i> , 2017, 7, 16823-16825.	3.6	4
10	Room temperature ferromagnetic and semiconducting properties of graphene adsorbed with cobalt oxide using electrochemical method. <i>Journal of Magnetism and Magnetic Materials</i> , 2017, 444, 361-363.	2.3	0
11	Structural and optical characterization of MoS ₂ quantum dots defined by thermal annealing. <i>Journal of Luminescence</i> , 2017, 183, 62-67.	3.1	29
12	Room temperature ferromagnetic and ambipolar behaviors of MoS ₂ doped by manganese oxide using an electrochemical method. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	7
13	Controllable Growth of Single Layer MoS ₂ and Resistance Switching Effect in Polymer/MoS ₂ Structure. <i>Applied Science and Convergence Technology</i> , 2017, 26, 129-132.	0.9	1
14	Toward negligible charge loss in charge injection memories based on vertically integrated 2D heterostructures. <i>Nano Research</i> , 2016, 9, 2319-2326.	10.4	36
15	Resistive switching memory device with metal oxide quantum dots on a graphene layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 325-328.	1.8	0
16	Electrically Tunable and Negative Schottky Barriers in Multi-layered Graphene/MoS ₂ Heterostructured Transistors. <i>Scientific Reports</i> , 2015, 5, 13743.	3.3	55
17	Structural and optical properties of MoS ₂ layers grown by successive two-step chemical vapor deposition method. <i>Thin Solid Films</i> , 2015, 587, 47-51.	1.8	16
18	Transport properties of unrestricted carriers in bridge-channel MoS ₂ field-effect transistors. <i>Nanoscale</i> , 2015, 7, 17556-17562.	5.6	14